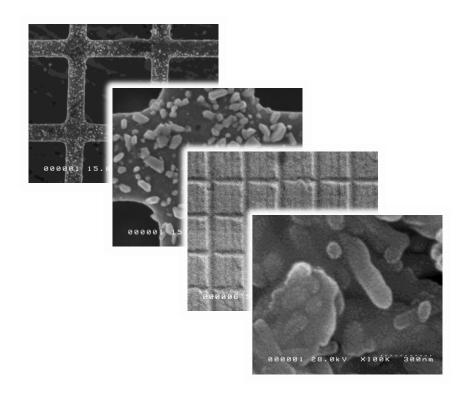
Experimental setup for proof of concept

- High probe current with high resolution for high throughput
- Extreme small energy dispersion for brighter e-beam

PC-SEM: CFE e-gun replaced with PeS product e-gun on the conventional SEM system

The conventional SEM replaced with PeS product egun (**PC-SEM** system) consists of a photocathode egun with the laser and a photo-electron beam adjustment system and the SEM.

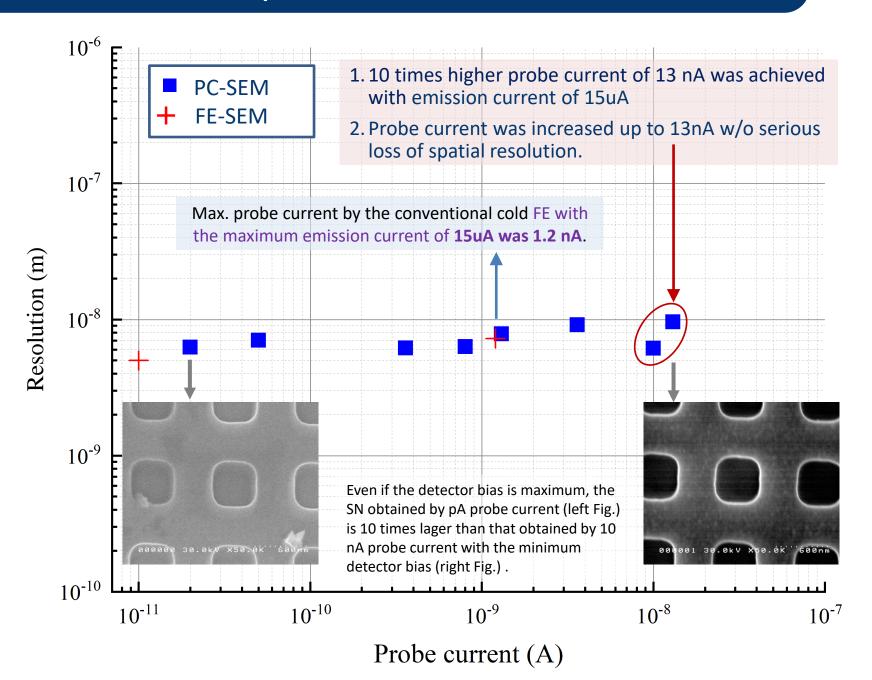
The beam axis, convergence, and divergence of the electron beam into the SEM column were optimized by the e-beam adjuster.





Measurement data - High probe current with high resolution for high throughput -

Result: Probe current dependence based on 10 nm resolution

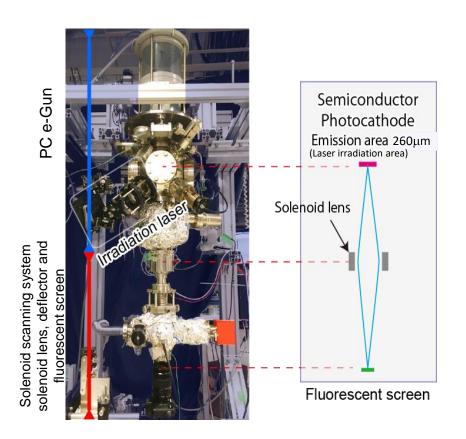


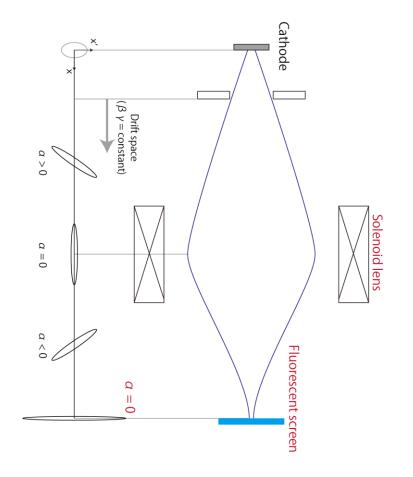
Measurement data

- Extreme small energy dispersion for brighter e-beam -

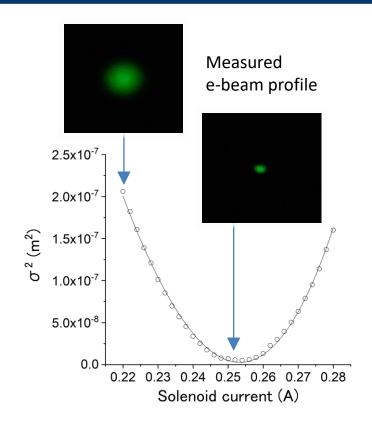
Measurement of electron energy dispersion by solenoid scan method

Brightness, electron energy dispersion (k_BT) can be calculated by the geometric emittance. Geometric emittance evaluation by measurement of beam envelope around focus point.





Results of electron energy dispersion by solenoid scan method



- Measurement of beam size (σ) dependence on solenoid coil current (i)
- Calculation of beam envelope by the following fitting function:

$$\sigma^2 = A(i^2 - B)^2 + C$$
A, B, C are fitting parameters

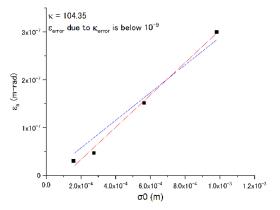
Geometric emittance can be expressed by fitting parameters:

$$\varepsilon = \frac{\sqrt{AC}}{L^2 \kappa'}, \frac{1}{f} = \kappa I^2$$

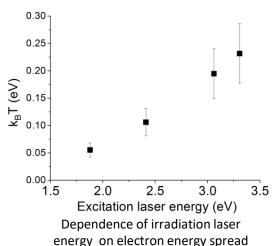
Brightness and k_RT:

$$B = \frac{I}{(\pi \varepsilon)^2}, \ \varepsilon = \frac{\sigma_0}{\beta \gamma} \sqrt{\frac{k_B T}{mc^2}}$$

I: emission current, σ_0 : emission size



Dependence of irradiation laser energy on e-beam emittance.



Electron energy dispersion:

0.05eV (AlGaAs) 0.08eV (InGaN)

*Energy spread of the cold FE: 0.3 eV

"Observation of a 0.055 nm Spacing Lattice Image in Gold", Takeshi K AWASAKI, Tsuyoshi MATSUDA, Junji ENDO and Akira TONOMURA, J APANESE JOURNAL OF APPLIED PHYSICS, VOL. 29, No. 3, pp. L 5